



## TO-92 Plastic-Encapsulate Transistors

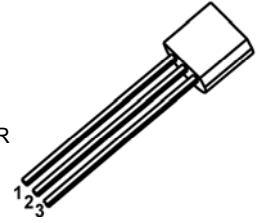
**2SC2130** TRANSISTOR (NPN)

### FEATURES

- High DC Current Gain

TO - 92

1. EMITTER
2. COLLECTOR
3. BASE



### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	45	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current	0.8	A
$P_C$	Collector Power Dissipation	600	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	208	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	45			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35\text{V}, I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=25\text{V}, I_B=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=20\text{mA}$			0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$			0.8	V
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			13	pF
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	100			MHz

### CLASSIFICATION OF $h_{FE}$

RANK	O	Y
RANGE	100-200	160-320

# Typical Characteristics

# 2SC2130

